

2MBI900VXA-120E-50

IGBT Modules

IGBT MODULE (V series) 1200V / 900A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units		
	Collector-Emitter voltage		Vces			1200	V	
	Gate-Emitter voltage		V _{GES}			±20	V	
<u>_</u>	Collector current		Ic	Continuous	Tc=25°C	1200		
rter					Tc=100°C	900		
Inve			C pulse	1ms		1800	Α	
=			-lc			900		
			-I _{C pulse}	1ms		1800		
	Collector power dissipation		Pc	1 device		5100	W	
Junction temperature			Tj			175	°C	
Operating junction temperature (under switching conditions)			Tjop			150		
Case temperature			Tc			150		
Storage temperature		T _{stg}			-40 ~ +150			
le ol	olation voltage	between terminal and copper base (*1)	V.	AC : 1min.		4000	VAC	
1501		between thermistor and others (*2)	Viso			4000		
	rew torque (*3)	Mounting	-	M5		6.0		
Scre		Main Terminals	-	M8 M4		10.0	N m	
		Sense Terminals	-			2.1		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value : Mounting Recommendable Value : Main Terminals Recommendable Value : Sense Terminals 3.0 ~ 6.0 Nm 8.0 ~ 10.0 Nm 1.8 ~ 2.1 Nm (M5) (M8)

Electrical characteristics (at T_i= 25°C unless otherwise specified)

Items		Comple e le	Symbola Canditions			Characteristics		
		Symbols	Symbols Conditions		min.	typ.	max.	Units
	Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	8.0	mA
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	1600	nA
Inverter	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 900mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	V _{CE (sat)}		T _j =25°C	-	1.85	2.30	V
		(terminal)		T _j =125°C	-	2.15	-	
		(*4)	V _{GE} = 15V Ic = 900A	T _j =150°C	-	2.20	-	
		V		T _j =25°C	-	1.75	2.20	
		V _{CE (sat)} (chip)		T _j =125°C	-	2.05	-	
				T _j =150°C	-	2.10	-	
	Internal gate resistance	R _G (int)	-		-	1.19	-	Ω
	Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	83	-	nF
	Turn-on time	ton	Vcc = 600V	-	1000	-	nsec	
		t r	Ic = 900A	-	400	-		
		t _{r (i)}	V _{GE} = ±15V	-	150	-		
	Turn-off time	toff	$R_G = 1.6\Omega$	-	1200	-		
	Turn-on time	t _f	Ls = 70nH	-	150	-		
	Forward on voltage	VF		T _j =25°C	-	1.90	2.35	
		(terminal)		T _j =125°C	-	2.05	-	
		(*4)	V _{GE} = 0V	T _j =150°C	-	2.00	-	V
		.,	I _F = 900A	T _j =25°C	-	1.80	2.25] v
		V _F		T _j =125°C	-	1.95	-	
		(chip)		T _j =150°C	-	1.90	-	1
	Reverse recovery time	recovery time t_{rr} $l_F = 900A$		-	200	-	nsec	
ţoţ	Resistance	R	T = 25°C T = 100°C		-	5000	-	Ω
Thermistor	Resistance	K			465	495	520	
를	B value	В	T = 25/50°C		3305	3375	3450	K

Note *4: Fuji defined VoE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

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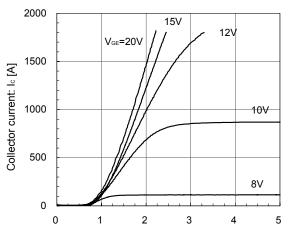
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
items			min.	typ.	max.	Units
Thermal resistance(1device)	R _{th(j-c)}	Inverter IGBT	-	-	0.030	°C/W
Thermal resistance (Tuevice)		Inverter FWD	-	-	0.054	
Contact thermal resistance (1device) (*5)	R _{th(c-f)}	with Thermal Compound		0.00625	-	

Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

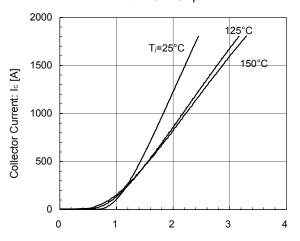
 $[INVERTER] \\ Collector current vs. Collector-Emitter voltage (typ.) \\ T_i = 25^{\circ}C \ / \ chip$



Collector-Emitter voltage: Vce [V]

[INVERTER]

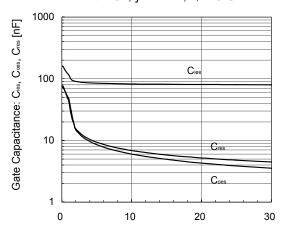
Collector current vs. Collector-Emitter voltage (typ.) V_{GE} = 15V / chip



Collector-Emitter Voltage: V_{CE} [V]

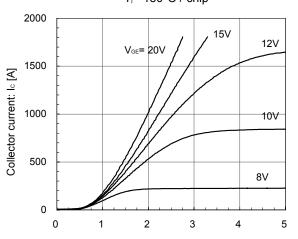
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) $V_{\text{GE}} = 0V, f = 1 \text{MHz}, T_{\text{J}} = 25^{\circ}\text{C}$



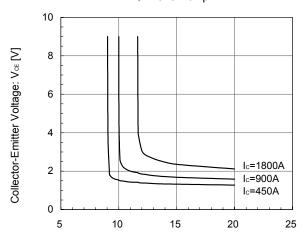
Collector-Emitter voltage: $V_{\text{CE}}[V]$

[INVERTER]
Collector current vs. Collector-Emitter voltage (typ.)
T,= 150°C / chip



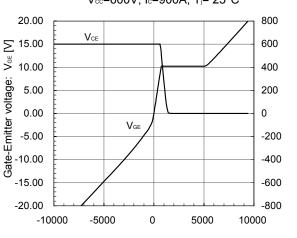
Collector-Emitter voltage: Vce [V]

[INVERTER]
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_i= 25°C / chip



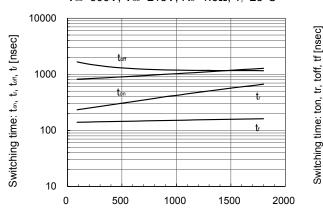
Gate-Emitter Voltage: VGE [V]

[INVERTER]
Dynamic Gate Charge (typ.)
V₀c=600V, I₀=900A, T,= 25°C



Gate charge: Q_9 [μ C]

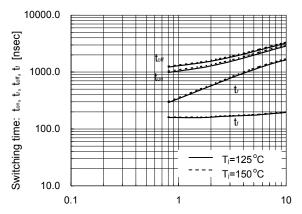
$[INVERTER] \\ Switching time vs. Collector current (typ.) \\ V_{cc}=600V, V_{ce}=\pm15V, R_c=1.6\Omega, T_i=25^{\circ}C$



Collector current: Ic [A]

[INVERTER]

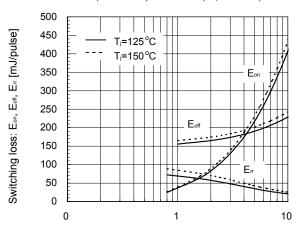
Switching time vs. Gate resistance (typ.) V_{cc}=600V, I_c=900A, V_{GE}= \pm 15V, T_i=125°C, 150°C



Gate resistance: R_G [Ω]

[INVERTER]

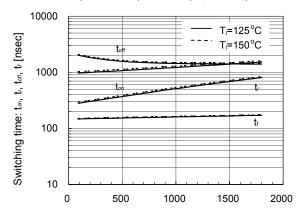
Switching loss vs. Gate resistance (typ.) V_{cc} =600V, I_c =900A, V_{ce} =±15V, T_i =125°C, 150°C



Gate resistance: $R_G [\Omega]$

[INVERTER]

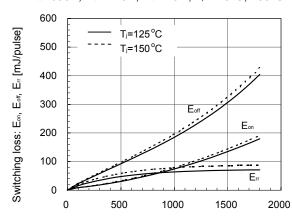
Switching time vs. Collector current (typ.) $V_{\text{CC}}=600V$, $V_{\text{CE}}=\pm15V$, $R_{\text{G}}=1.6\Omega$, $T_{\text{J}}=125^{\circ}C$, $150^{\circ}C$



Collector current: Ic [A]

[INVERTER]

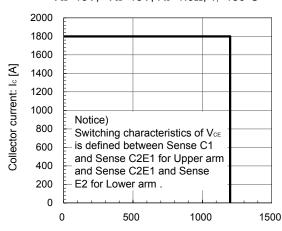
Switching loss vs. Collector current (typ.) V_{cc} =600V, V_{cs} =±15V, R_{c} =1.6 Ω , T_{j} =125°C, 150°C



Collector current: Ic [A]

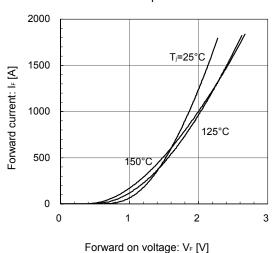
[INVERTER]

Reverse bias safe operating area (max.) $+V_{\text{GE}}=15V$, $-V_{\text{GE}}=15V$, $R_{\text{G}}=1.6\Omega$, $T_{\text{J}}=150^{\circ}\text{C}$

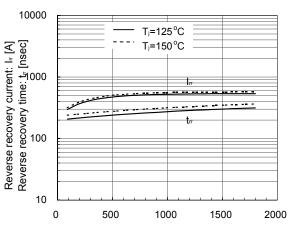


Collector-Emitter voltage: Vce [V]

[INVERTER]
Forward Current vs. Forward Voltage (typ.)
chip

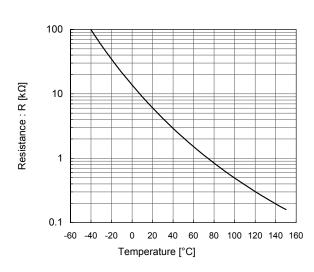


 $[INVERTER] \\ Reverse Recovery Characteristics (typ.) \\ V_{cc} = 600V, \ V_{cE} = \pm 15V, \ R_{c} = 1.6\Omega, \ T_{j} = 125^{\circ}C, \ 150^{\circ}C$

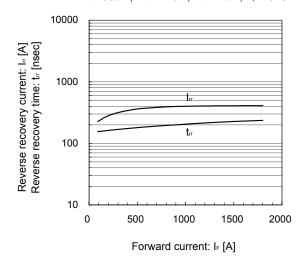


Forward current: I_F [A]

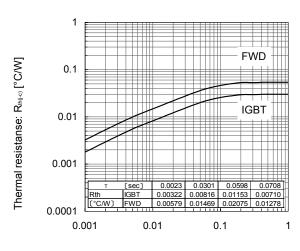
[THERMISTOR]
Temperature characteristic (typ.)



[INVERTER] Reverse Recovery Characteristics (typ.) V_{cc} =600V, V_{ee} =±15V, R_e =1.6 Ω , T_j =25°C

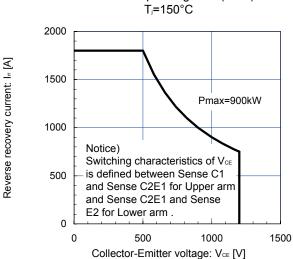


Transient Thermal Resistance (max.)

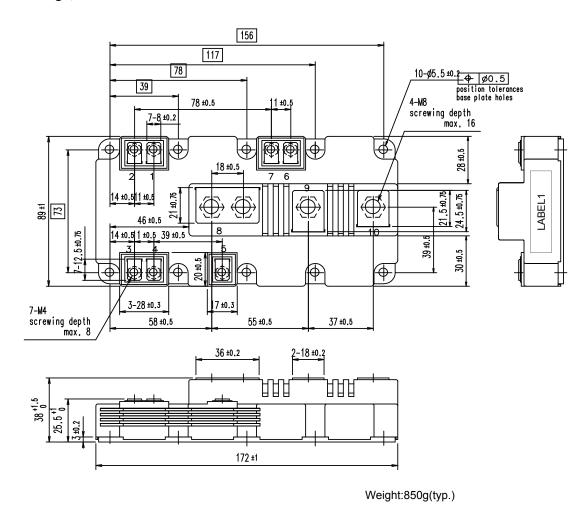


Pulse Width: Pw [sec]

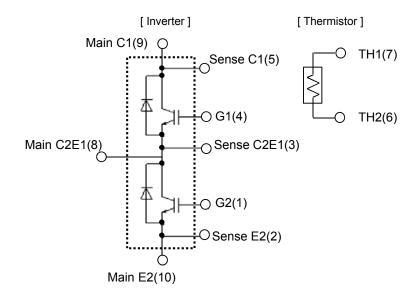
FWD safe operating area (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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- · OA equipment
- Communications equipment (terminal devices)
- Measurement equipment

- · Machine tools
- Audiovisual equipment Electrical home appliances
- Personal equipment Industrial robots etc.

· Gas leakage detectors with an auto-shut-off feature

Trunk communications equipment

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